

## 74F219 64-Bit Random Access Memory with 3-STATE Outputs

### General Description

The 74F219 is a high-speed 64-bit RAM organized as a 16-word by 4-bit array. Address inputs are buffered to minimize loading and are fully decoded on-chip. The outputs are 3-STATE and are in the high-impedance state whenever the Chip Select ( $\overline{CS}$ ) input is HIGH. The outputs are active only in the Read mode. This device is similar to the 74F189 but features non-inverting, rather than inverting, data outputs.

### Features

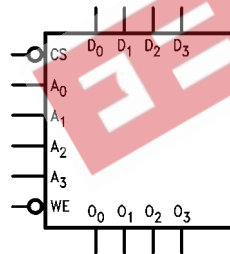
- 3-STATE outputs for data bus applications
- Buffered inputs minimize loading
- Address decoding on-chip
- Diode clamped inputs minimize ringing
- Available in SOIC (300 mil only)

### Ordering Code:

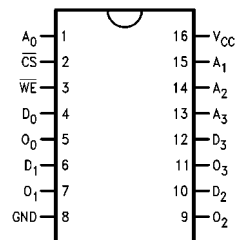
Order Number	Package Number	Package Description
74F219SC	M16B	16-Lead Small Outline Intergrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide
74F219SJ	M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74F219PC	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

### Logic Symbol



### Connection Diagram



## Unit Loading/Fan Out

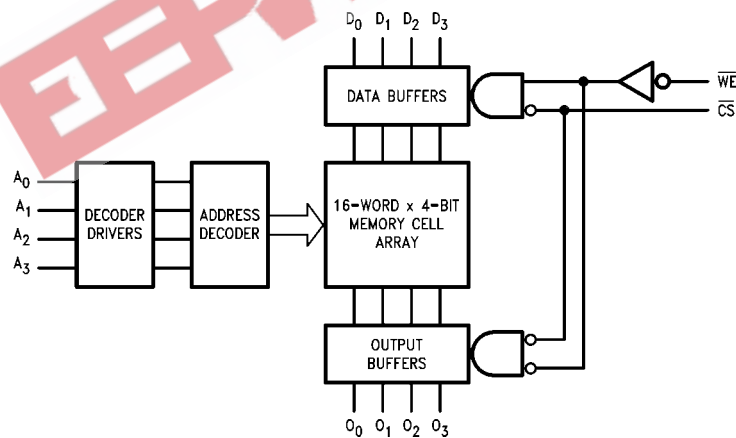
Pin Names	Description	U.L. HIGH/LOW	Input $I_{IH}/I_{IL}$ Output $I_{OH}/I_{OL}$
$A_0$ - $A_3$	Address Inputs	1.0/1.0	20 $\mu$ A/-0.6 mA
$\overline{CS}$	Chip Select Input (Active LOW)	1.0/2.0	20 $\mu$ A/-1.2 mA
$\overline{WE}$	Write Enable Input (Active LOW)	1.0/1.0	20 $\mu$ A/-0.6 mA
$D_0$ - $D_3$	Data Inputs	1.0/1.0	20 $\mu$ A/-0.6 mA
$O_0$ - $O_3$	3-STATE Data Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)

## Function Table

Inputs		Operation	Condition of Outputs
$\overline{CS}$	$\overline{WE}$		
L	L	Write	High Impedance
L	H	Read	True Stored Data
H	X	Inhibit	High Impedance

H = HIGH Voltage Level  
L = LOW Voltage Level  
X = Immaterial

## Block Diagram



Absolute Maximum Ratings (Note 1)		Recommended Operating Conditions	
Storage Temperature	-65°C to +150°C	Free Air Ambient Temperature	0°C to +70°C
Ambient Temperature under Bias	-55°C to +125°C	Supply Voltage	+4.5V to +5.5V
Junction Temperature under Bias	-55°C to +150°C		
V <sub>CC</sub> Pin Potential to Ground Pin	-0.5V to +7.0V		
Input Voltage (Note 2)	-0.5V to +7.0V		
Input Current (Note 2)	-30 mA to +5.0 mA		
Voltage Applied to Output in HIGH State (with V <sub>CC</sub> = 0V)			
Standard Output	-0.5V to V <sub>CC</sub>		
3-STATE Output	-0.5V to +5.5V		
Current Applied to Output in LOW State (Max)	twice the rated I <sub>OL</sub> (mA)		

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

**Note 2:** Either voltage limit or current limit is sufficient to protect inputs.

### DC Electrical Characteristics

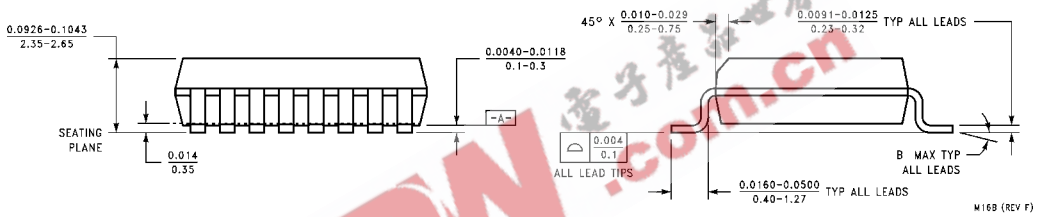
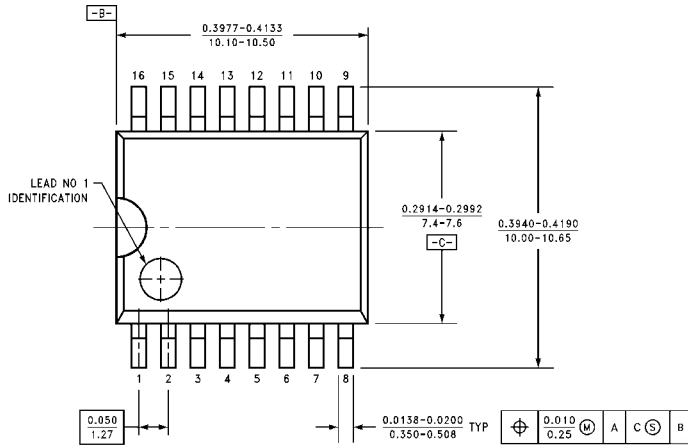
Symbol	Parameter	Min	Typ	Max	Units	V <sub>CC</sub>	Conditions
V <sub>IH</sub>	Input HIGH Voltage	2.0			V		Recognized as a HIGH Signal
V <sub>IL</sub>	Input LOW Voltage			0.8	V		Recognized as a LOW Signal
V <sub>CD</sub>	Input Clamp Diode Voltage			-1.2	V	Min	I <sub>IN</sub> = -18 mA
V <sub>OH</sub>	Output HIGH Voltage	10% V <sub>CC</sub>	2.5		V	Min	I <sub>OH</sub> = -1 mA
		10% V <sub>CC</sub>	2.4	I <sub>OH</sub> = -3 mA			
		5% V <sub>CC</sub>	2.7	I <sub>OH</sub> = -1 mA			
		5% V <sub>CC</sub>	2.7	I <sub>OH</sub> = -3 mA			
V <sub>OL</sub>	Output LOW Voltage			0.5	V	Min	I <sub>OL</sub> = 24 mA
I <sub>IH</sub>	Input HIGH Current			5.0	μA	Max	V <sub>IN</sub> = 2.7V
I <sub>BVI</sub>	Input HIGH Current Breakdown Test			7.0	μA	Max	V <sub>IN</sub> = 7.0V
I <sub>CEX</sub>	Output HIGH Leakage Current			50	μA	Max	V <sub>OUT</sub> = V <sub>CC</sub>
V <sub>ID</sub>	Input Leakage Test	4.75			V	0.0	I <sub>ID</sub> = 1.9 μA All Other Pins Grounded
I <sub>OD</sub>	Output Leakage Circuit Current			3.75	μA	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded
I <sub>IL</sub>	Input LOW Current			-0.6 -1.2	mA	Max	V <sub>IN</sub> = 0.5V (A <sub>n</sub> , $\overline{WE}$ , D <sub>n</sub> ) V <sub>IN</sub> = 0.5V (CS)
I <sub>OZH</sub>	Output Leakage Current			50	μA	Max	V <sub>OUT</sub> = 2.7V
I <sub>OZL</sub>	Output Leakage Current			-50	μA	Max	V <sub>OUT</sub> = 0.5V
I <sub>OS</sub>	Output Short-Circuit Current	-60		-150	mA	Max	V <sub>OUT</sub> = 0V
I <sub>ZZ</sub>	Bus Drainage Test			500	μA	0.0V	V <sub>OUT</sub> = 5.25V
I <sub>CC</sub>	Power Supply Current		37	55	mA	Max	

AC Electrical Characteristics									
Symbol	Parameter	$T_A = +25^\circ\text{C}$ $V_{CC} = +5.0\text{V}$ $C_L = 50\text{ pF}$			$T_A = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = +5.0\text{V}$ $C_L = 50\text{ pF}$		$T_A = 0^\circ\text{C to } +70^\circ\text{C}$ $V_{CC} = +5.0\text{V}$ $C_L = 50\text{ pF}$		Units
		Min	Typ	Max	Min	Max	Min	Max	
$t_{PLH}$	Access Time, HIGH or LOW	10.0	18.5	26.0	9.0	32.0	10.0	27.0	ns
$t_{PHL}$	$A_n$ to $O_n$	8.0	13.5	19.0	8.0	23.0	8.0	20.0	
$t_{PZH}$	Access Time, HIGH or LOW	3.5	6.0	8.5	3.5	10.5	3.5	9.5	ns
$t_{PZL}$	$\overline{CS}$ to $O_n$	5.0	9.0	13.0	5.0	15.0	5.0	14.0	
$t_{PHZ}$	Disable Time, HIGH or LOW	2.0	4.0	6.0	2.0	8.0	2.0	7.0	ns
$t_{PLZ}$	$\overline{CS}$ to $O_n$	3.0	5.5	8.0	2.5	10.0	3.0	9.0	
$t_{PZH}$	Write Recovery Time	6.5	20.0	28.0	6.5	37.5	6.5	29.0	ns
$t_{PZL}$	HIGH or LOW, $\overline{WE}$ to $O_n$	6.5	11.0	15.5	6.5	17.5	6.5	16.5	
$t_{PHZ}$	Disable Time, HIGH or LOW	4.0	7.0	10.0	3.5	12.0	4.0	11.0	ns
$t_{PLZ}$	$\overline{WE}$ to $O_n$	5.0	9.0	13.0	5.0	15.0	5.0	14.0	

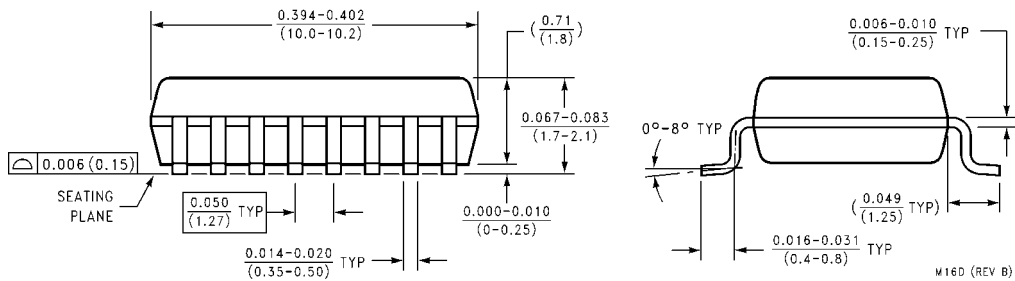
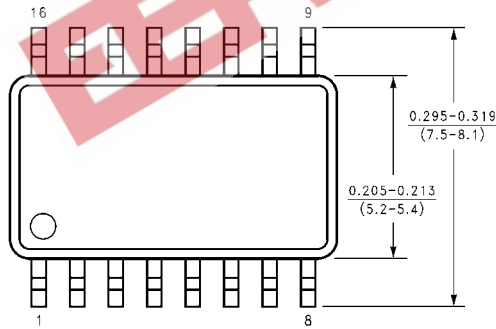
  

AC Operating Requirements								
Symbol	Parameter	$T_A = +25^\circ\text{C}$ $V_{CC} = +5.0\text{V}$		$T_A = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = +5.0\text{V}$		$T_A = 0^\circ\text{C to } +70^\circ\text{C}$ $V_{CC} = +5.0\text{V}$		Units
		Min	Max	Min	Max	Min	Max	
$t_S(H)$	Setup Time, HIGH or LOW	0		0		0		ns
$t_S(L)$	$A_n$ to $\overline{WE}$	0		0		0		
$t_H(H)$	Hold Time, HIGH or LOW	2.0		2.0		2.0		ns
$t_H(L)$	$A_n$ to $\overline{WE}$	2.0		2.0		2.0		
$t_S(H)$	Setup Time, HIGH or LOW	10.0		11.0		10.0		ns
$t_S(L)$	$D_n$ to $\overline{WE}$	10.0		11.0		10.0		
$t_H(H)$	Hold Time, HIGH or LOW	0		2.0		0		ns
$t_H(L)$	$D_n$ to $\overline{WE}$	0		2.0		0		
$t_S(L)$	Setup Time, LOW $\overline{CS}$ to $\overline{WE}$	0		0		0		ns
$t_H(L)$	Hold Time, LOW $\overline{CS}$ to $\overline{WE}$	6.0		7.5		6.0		
$t_W(L)$	$\overline{WE}$ Pulse Width, LOW	6.0		15.0		6.0		ns

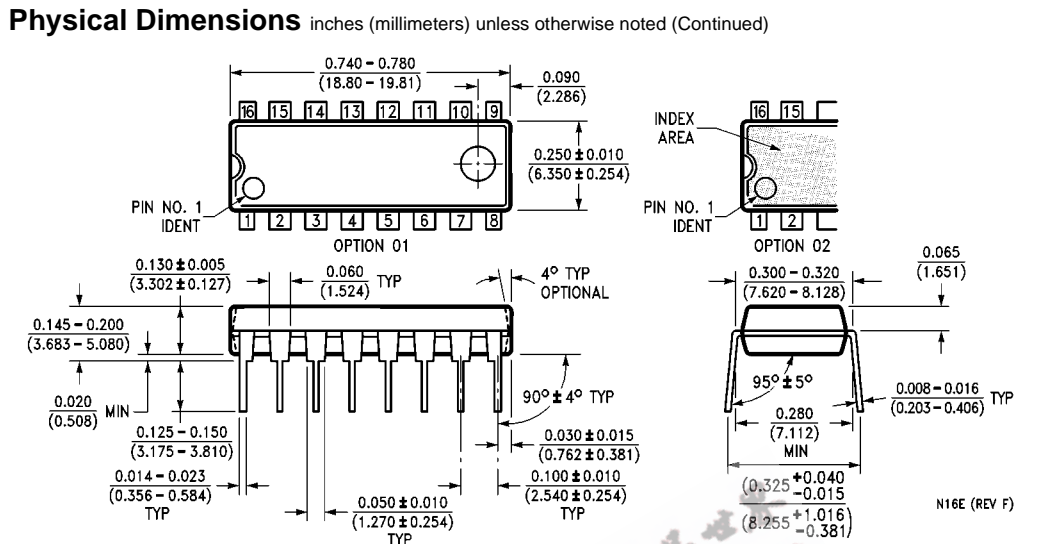
**Physical Dimensions** inches (millimeters) unless otherwise noted



**16-Lead Small Outline Intergrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide  
Package Number M16B**



**16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide  
Package Number M16D**



16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide  
Package Number N16E

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